UTG40N65LSS2

**Advance** 

Insulated Gate Bipolar Transistor

# 650V, SMPS N-CHANNEL IGBT

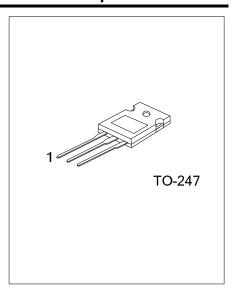
#### DESCRIPTION

The UTC **UTG40N65LSS2** is a N-channel IGBT. it uses UTC's advanced technology to provide customers with high input impedance, high switching speed and low conduction loss, etc.

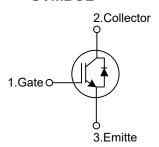
The UTC **UTG40N65LSS2** is suitable for high voltage switching, high frequency switch mode power supplies.

#### ■ FEATURES

- \* High switching speed
- \* High avalanche ruggedness
- \* Low saturation voltage:  $V_{CE(SAT).Typ.}$ =1.9V @ Ic=40A,  $V_{GE}$ =15V (T<sub>C</sub> =25°C)



#### ■ SYMBOL



### ■ ORDERING INFORMATION

Ordering Number		Daalaaaa	Pin	Assignm	Da alsia a		
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTG40N65LSS2L-T47-T	UTG40N65LSS2G-T47-T	TO-247	G	С	Е	Tube	

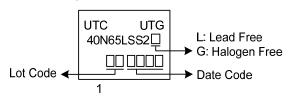
Note: Pin Assignment: G: Gate C: Collector E: Emitter

UTG40N65LSS2G-T47-T (1)Packing Type (1) T: Tube

(2)Package Type (2) T47: TO-247

(3)Green Package (3) G: Halogen Free and Lead Free, L: Lead Free

### ■ MARKING



www.unisonic.com.tw 1 of 4

### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Emitter Voltage		V <sub>CES</sub>	650	V	
Gate-Emitter Voltage		\/	±20	V	
Transient Gate-emitter voltage (tp < 5 ms)		$V_{GES}$	±25	V	
Continuous Collector Current	T <sub>C</sub> =25°C	Ic	80	Α	
	T <sub>C</sub> =100°C		40	Α	
Collector Current Pulsed (Note 1)		I <sub>CM</sub>	160	Α	
Diode Forward Current	T <sub>C</sub> =25°C	l <sub>F</sub>	80	Α	
Diode Forward Current	T <sub>C</sub> =100°C		40	Α	
Short Circuit Withstand Time		tsc			
V <sub>GE</sub> = 15V, V <sub>CC</sub> ≤ 200V					
Allowed number of short circuits < 1000			3	μs	
Time between short circuits: ≥ 1.0s					
$T_{VJ} = 25^{\circ}C$					
Power Dissipation (T <sub>C</sub> =25°C)		P <sub>D</sub>	300	W	
Operating Junction Temperature		$T_J$	-40 ~ +150	°C	
Storage Temperature Range		T <sub>STG</sub>	-55 ~ +150	°C	

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

### **■ THERMAL DATA**

PARAMETER	SYMBOL	RATING	UNIT
Junction to Case	θ.ιс	0.57	°C/W

<sup>2.</sup> Pulse width limited by maximum junction temperature.

## ■ **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub>=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Off Characteristics	STIVIDOL	- TEST CONDITIONS   WIIN   TTP   WAX				UNIT	
	D\/			650			V
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	), oso,, ,, o,,		650		50	
Collector Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> =650V, V <sub>GE</sub> =0V				50	μA
G-E Leakage Current	Leakage Current I <sub>GES</sub> V <sub>CE</sub> =0V, V <sub>GE</sub> =±20V					±100	nA
On Characteristics						1	
Gate to Emitter Threshold Voltage	$V_{\text{GE(TH)}}$	I <sub>C</sub> =1mA, V <sub>CE</sub> =V <sub>GE</sub>	<sub>C</sub> =1mA, V <sub>CE</sub> =V <sub>GE</sub>		5.0	6.0	V
0-1144- 5	V <sub>CE(SAT)</sub>	I <sub>C</sub> =40A, V <sub>GE</sub> =15V	T <sub>C</sub> =25°C		1.9		V
Collector to Emitter Saturation Voltage			T <sub>C</sub> =125°C		2.6		V
Dynamic Characteristics							
Input Capacitance	C <sub>IES</sub>	V <sub>CE</sub> =30V, V <sub>GE</sub> =0V, f=1MHz			2480		рF
Output Capacitance	C <sub>OES</sub>				95		рF
Reverse Transfer Capacitance	C <sub>RES</sub>				21		pF
Switching Characteristics							
Total Gate Charge	$Q_{G}$				78		nC
Gate-Emitter Charge	$Q_GE$	V <sub>CE</sub> =520V, I <sub>C</sub> =40A, V <sub>GE</sub> =15V					nC
Gate-Collector Charge	Q <sub>GC</sub>						nC
Turn-On Delay Time	t <sub>DON)</sub>				32		ns
Rise Time	t <sub>R</sub>	],,,,,,,,,,,	1		55		ns
Turn-Off Delay Time	t <sub>DOFF)</sub>	-V <sub>CC</sub> =400V, I <sub>C</sub> =40A, R <sub>G</sub> =10Ω, -V <sub>GE</sub> =0~15V -Inductive Load			106		ns
Fall Time	t <sub>F</sub>				51		ns
Turn-On Switching Loss	Eon				0.9		mJ
Turn-Off Switching Loss	E <sub>OFF</sub>	7			0.5		mJ
SOURCE- DRAIN DIODE RATINGS A		TERISTICS		•			
Forward Voltage Drop	VF	I <sub>F</sub> =40A			2.4		V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =40A, dI/dt=100A/μS, V <sub>CC</sub> =400V			68		ns
Reverse Recovery Charge	Qrr				522		nC

#### ■ TEST CIRCUIT AND WAVEFORMS

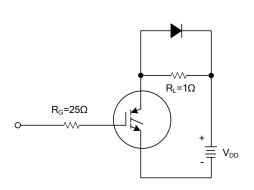


Fig 1. INDUCTIVE SWITCHING TEST CIRCUIT

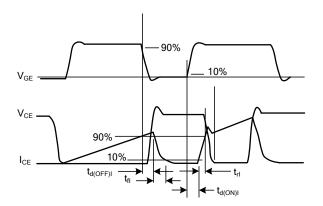


Fig 2. SWITCHING TEST WAVEFORMS

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.